



## Description

The AP4062CMT uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



DFN5X6-8L

## General Features

$V_{DS} = 30\text{ V}$   $I_D = 120\text{ A}$

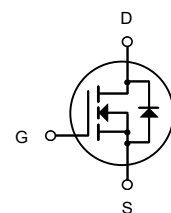
$R_{DS(ON)} < 4.4\text{ m}\Omega$   $V_{GS} = 10\text{ V}$

## Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

## Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
AP4062CMT	DFN5X6-8L	HXY MOSFET	5000

## Absolute Maximum Ratings ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}^{1,6}$	120	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}^{1,6}$	66	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	320	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	180	mJ
$I_{AS}$	Avalanche Current	60	A
$P_D @ T_C = 25^\circ\text{C}$	Total Power Dissipation <sup>4</sup>	187	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	62	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	1.1	$^\circ\text{C/W}$

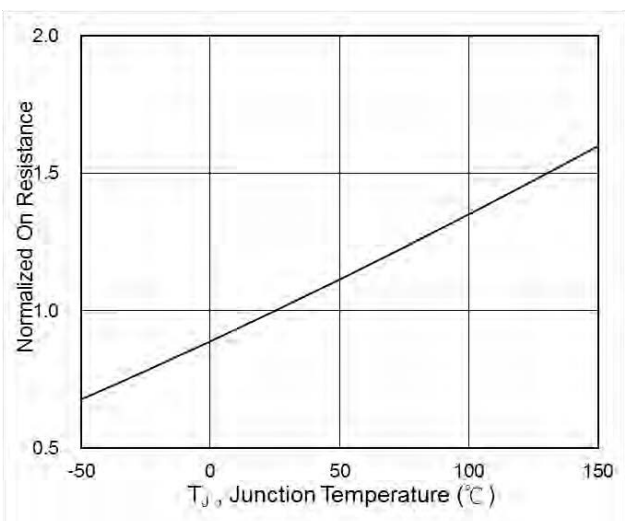
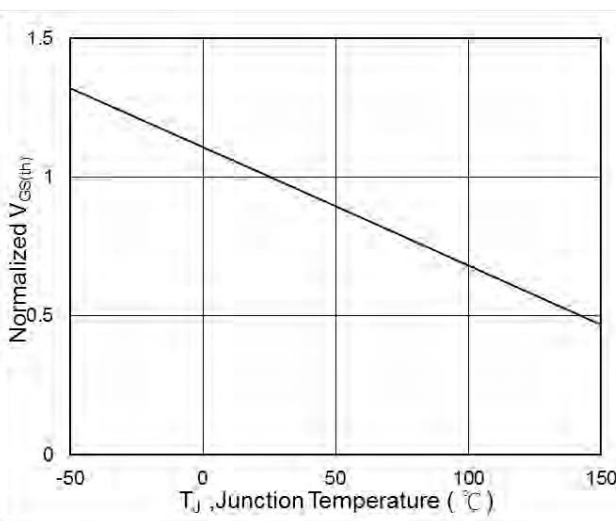
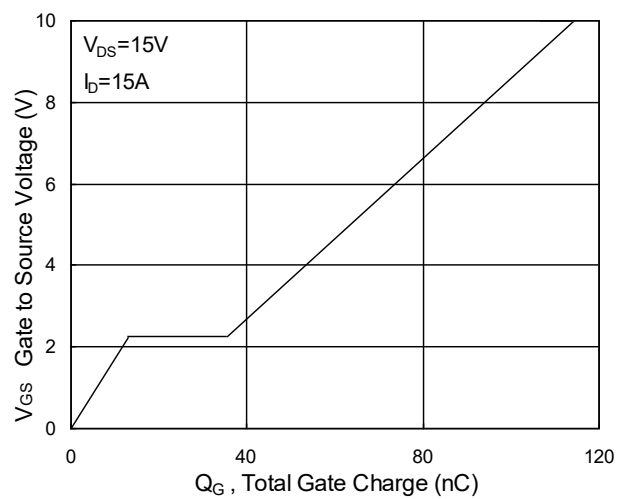
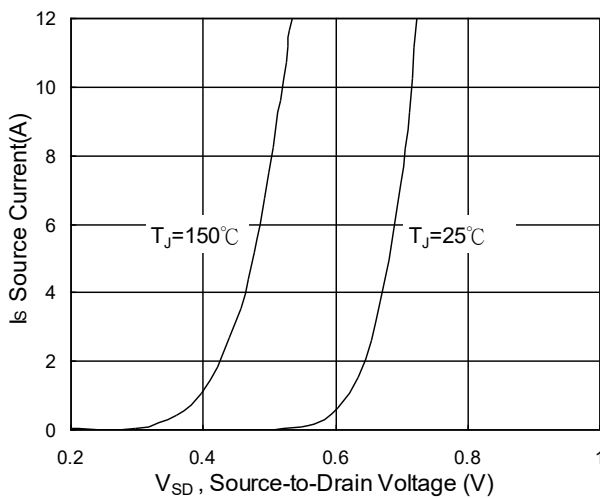
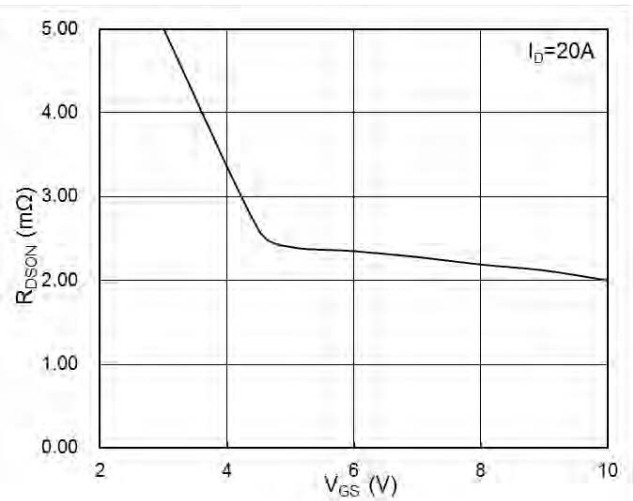
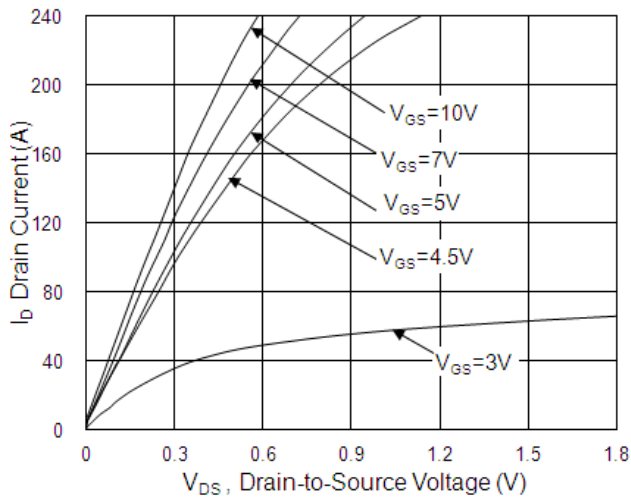


Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V$ , $I_D=250\mu A$	30	---	---	V
$\frac{\partial BV_{DS}}{\partial T_J}$	$BV_{DS}$ Temperature Coefficient	Reference to $25^\circ\text{C}$ , $I_D=1mA$	---	0.014	---	$V/^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V$ , $I_D=30A$	---	3.5	4.4	$m\Omega$
		$V_{GS}=4.5V$ , $I_D=15A$	---	4.6	5.8	
$V_{GS(th)}$	Gate Threshold Voltage		1.2	---	2.5	V
$\frac{\partial V_{GS(th)}}{\partial T_J}$	$V_{GS(th)}$ Temperature Coefficient	$V_{GS}=V_{DS}$ , $I_D=250\mu A$	---	-4	---	$mV/^\circ\text{C}$
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=24V$ , $V_{GS}=0V$ , $T_J=25^\circ\text{C}$	---	---	1	$\mu A$
		$V_{DS}=24V$ , $V_{GS}=0V$ , $T_J=55^\circ\text{C}$	---	---	5	
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V$ , $V_{DS}=0V$	---	---	$\pm 100$	nA
gfs	Forward Transconductance	$V_{DS}=5V$ , $I_D=30A$	---	50	---	S
$R_g$	Gate Resistance	$V_{DS}=0V$ , $V_{GS}=0V$ , $f=1MHz$	---	1.7	---	$\Omega$
$Q_g$	Total Gate Charge (4.5V)	$V_{DS}=15V$ , $V_{GS}=10V$ , $I_D=15A$	---	56.9	---	nC
$Q_{gs}$	Gate-Source Charge		---	13.8	---	
$Q_{gd}$	Gate-Drain Charge		---	23.5	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V$ , $V_{GS}=10V$ , $R_G=3.3\Omega$ , $I_D=1A$	---	20.1	---	ns
$T_r$	Rise Time		---	6.3	---	
$T_{d(off)}$	Turn-Off Delay Time		---	124.6	---	
$T_f$	Fall Time		---	15.8	---	
$C_{iss}$	Input Capacitance	$V_{DS}=15V$ , $V_{GS}=0V$ , $f=1MHz$	---	4345	---	pF
$C_{oss}$	Output Capacitance		---	340	---	
$C_{rss}$	Reverse Transfer Capacitance		---	225	---	
$I_S$	Continuous Source Current <sup>1,6</sup>	$V_G=V_D=0V$ , Force Current	---	---	85	A
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V$ , $I_S=1A$ , $T_J=25^\circ\text{C}$	---	---	1.2	V



## Typical Characteristics



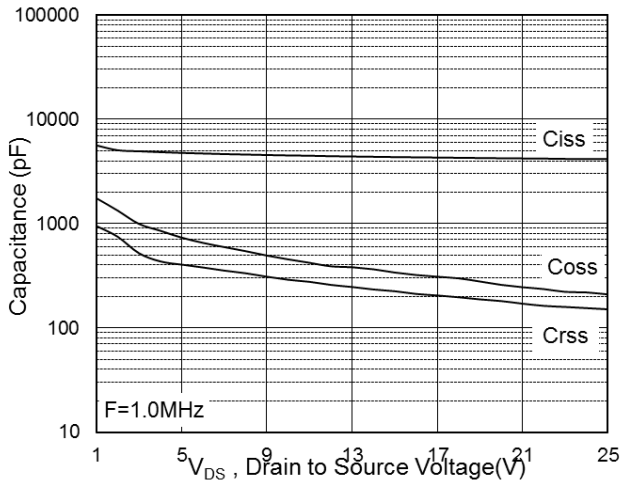


Fig.7 Capacitance

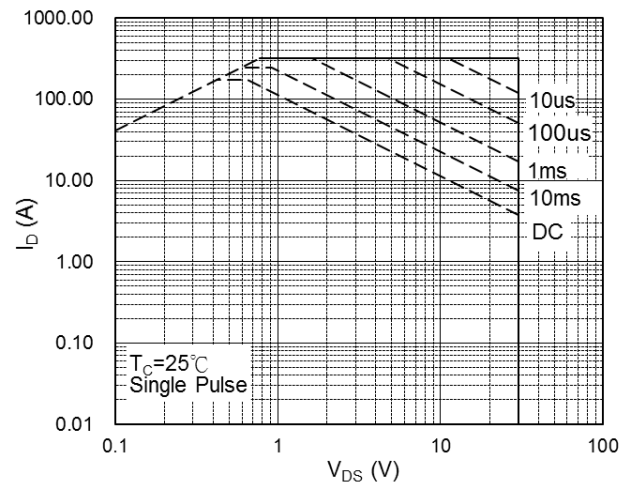


Fig.8 Safe Operating Area

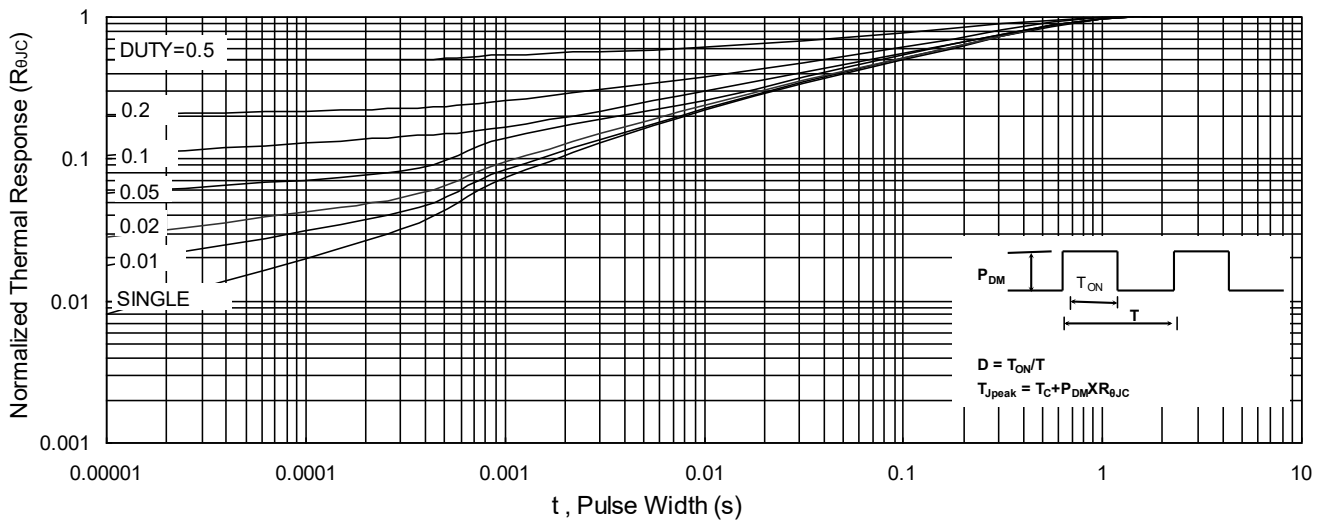


Fig.9 Normalized Maximum Transient Thermal Impedance

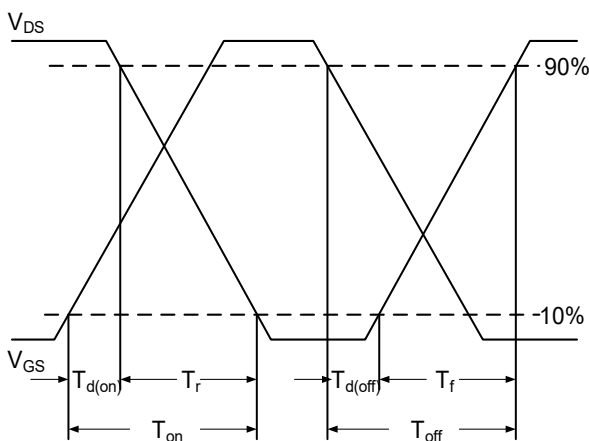


Fig.10 Switching Time Waveform

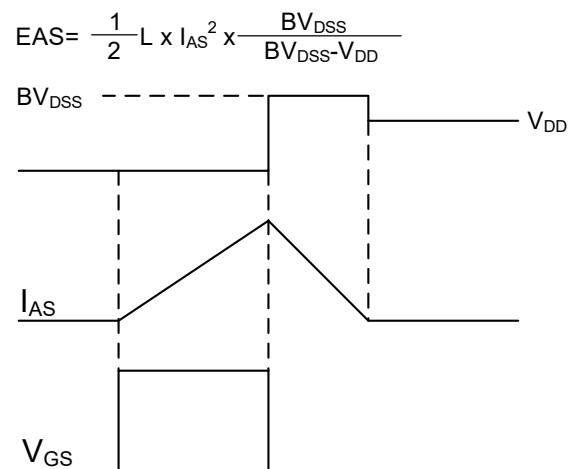
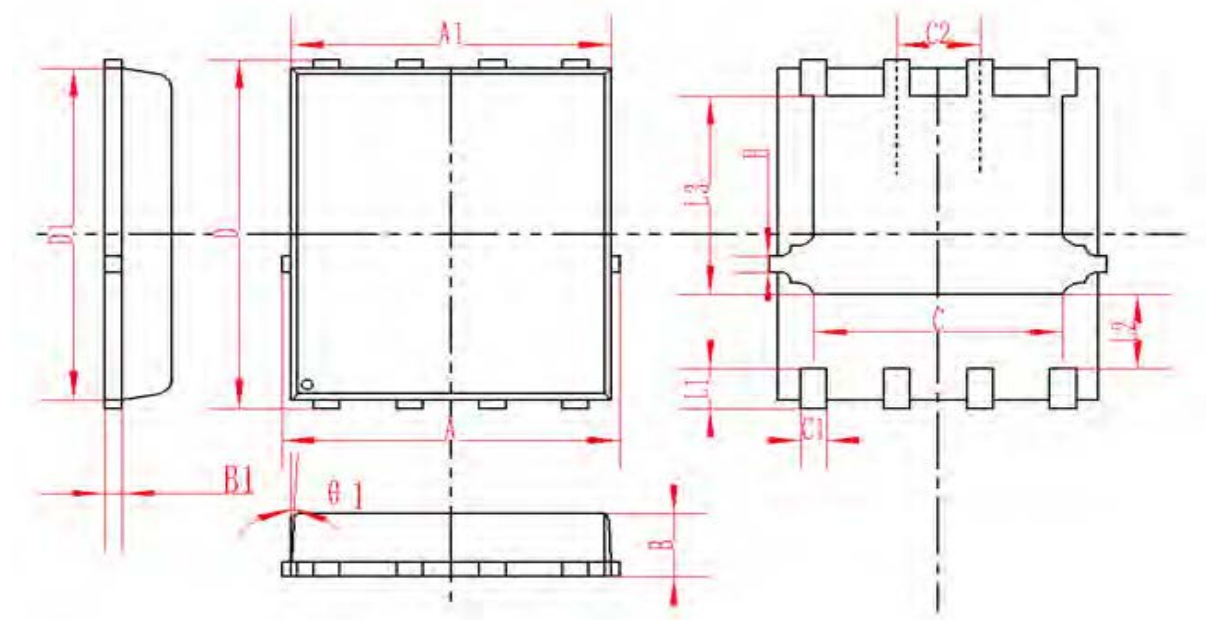


Fig.11 Unclamped Inductive Switching Waveform



## DFN5X6-8L Package Information



SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	5.3	5.5	5.7	0.208	0.216	0.224
A1	5.1	5.2	5.3	0.2	0.204	0.209
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.85	6.05	6.25	0.23	0.238	0.246
B	0.85	0.95	1.05	0.033	0.037	0.041
B1	0.254REF			0.010REF		
C	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2	1.27TYP			0.5TYP		
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
H	0.24	0.25	0.26	0.009	0.010	0.010



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